Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{GS}$	gate-source voltage			-8	_	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	-500	mA

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	<u>654</u>	D1 D2
2	G1	gate TR1		
3	D2	drain TR2	0	G1 $G2$ $G2$
4	S2	source TR2	∐1 ∐2 ∐3	
5	G2	gate TR2	TSSOP6 (SOT363)	
6	D1	drain TR1		S1 S2 017aaa262

# 6. Ordering information

Table 3. Ordering information

	Type number	Package	kage					
		Name	Description	Version				
	PMGD290UCEA	TSSOP6	plastic surface-mounted package; 6 leads	SOT363				

# 7. Marking

Table 4. Marking codes

rabio 4. marking codoc	
Type number	Marking code
	[1]
PMGD290UCEA	YD%

<sup>[1] % =</sup> placeholder for manufacturing site code

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit	
TR1 (N-channe	TR1 (N-channel)						
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V	
V <sub>GS</sub>	gate-source voltage			-8	8	V	

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Symbol	Parameter	Conditions		Min	Max	Unit
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	725	mA
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	450	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs		-	3	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	280	mW
			[1]	-	320	mW
		T <sub>sp</sub> = 25 °C		-	990	mW
TR1 (N-cha	nnel), Source-drain diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	370	mA
TR1 N-chai	nnel), ESD maximum rating					
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V
TR2 (P-cha	nnel)		-		,	,
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	in current $V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}$	[1]	-	-500	mA
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-320	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs		-	-2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	280	mW
			[1]	-	320	mW
		T <sub>sp</sub> = 25 °C		-	990	mW
TR2 (P-cha	nnel), Source-drain diode					
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	-370	mA
TR2 (P-cha	nnel), ESD maximum rating					
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V
Per device						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	445	mW
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> 

Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>. Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard [2]

Measured between all pins.

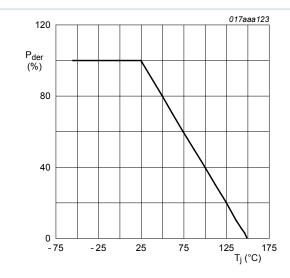


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

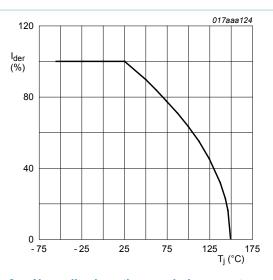
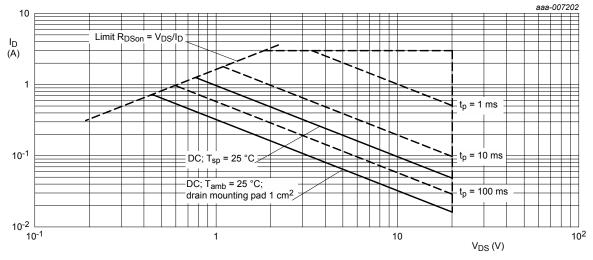


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



I<sub>DM</sub> = single pulse

Fig. 3. TR1 (N-channel): safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

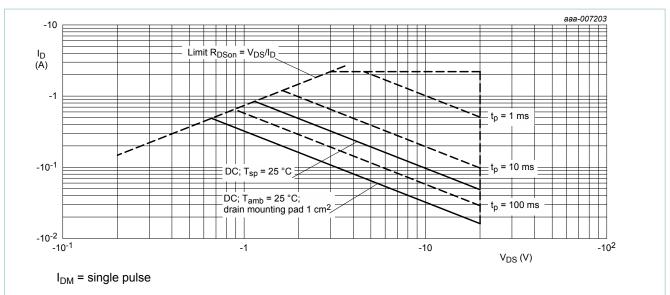


Fig. 4. TR2 (P-channel): safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

# 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
TR1 (N-cha	nnel)						
R <sub>th(j-a)</sub>	<sub>j-a)</sub> thermal resistance in free air		[1]	-	390	445	K/W
	from junction to ambient		[2]	-	340	390	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	130	K/W
TR2 (P-cha	nnel)		,			'	,
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	390	445	K/W
	from junction to ambient		[2]	-	340	390	K/W
$R_{\text{th(j-sp)}}$	thermal resistance from junction to solder point			-	-	130	K/W
Per device			,	'			_
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	300	K/W

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

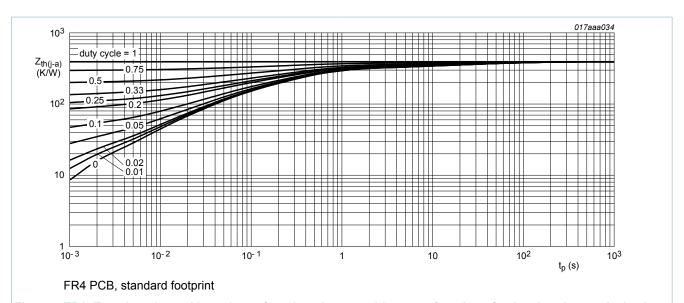
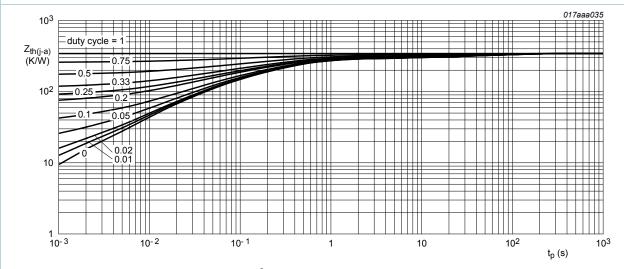


Fig. 5. TR1: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>.

Fig. 6. TR1: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

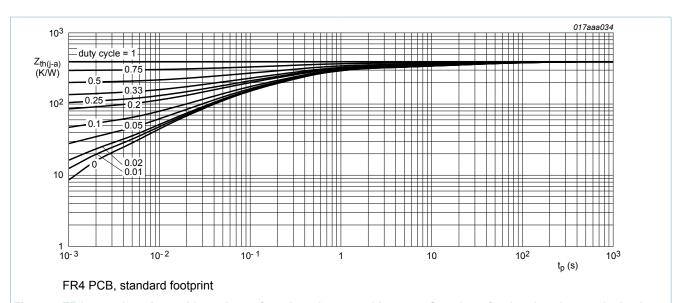


Fig. 7. TR2: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

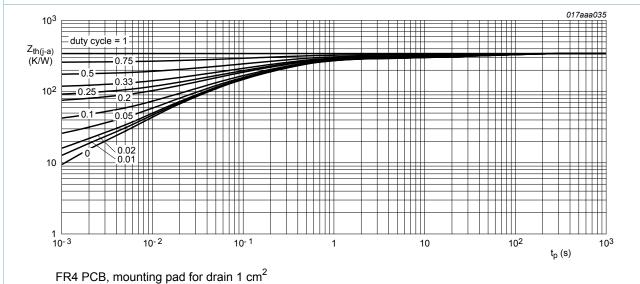


Fig. 8. TR2: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

# 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
TR1 (N-cha	nnel), Static characteristic	s	·			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D$ = 250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}$	0.5	0.75	0.95	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	10	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; -40 °C < T <sub>j</sub> < 150 °C	-	-	10	μA
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; -40 °C < T <sub>j</sub> < 150 °C	-	-	-10	μA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 500 mA; T <sub>j</sub> = 25 °C	-	290	380	mΩ
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 500 mA; T <sub>j</sub> = 150 °C	-	460	610	mΩ
		$V_{GS}$ = 2.5 V; $I_D$ = 200 mA; $T_j$ = 25 °C	-	420	620	mΩ
		$V_{GS}$ = 1.8 V; $I_D$ = 10 mA; $T_j$ = 25 °C	-	0.6	1.1	Ω
9 <sub>fs</sub>	transfer conductance	$V_{DS}$ = 10 V; $I_{D}$ = 200 mA; $T_{j}$ = 25 °C	-	1.6	-	S
TR1 (N-cha	nnel), Dynamic characteris	stics				
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 500 mA; V <sub>GS</sub> = 4.5 V;	-	0.45	0.68	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.15	-	nC
$Q_{GD}$	gate-drain charge		-	0.15	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	55	83	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	15	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	7	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 10 V; $R_L$ = 250 $\Omega$ ; $V_{GS}$ = 4.5 V;	-	6	12	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4	-	ns
$t_{d(off)}$	turn-off delay time		-	86	172	ns
t <sub>f</sub>	fall time		-	31	-	ns
TR1 (N-cha	nnel), Source-drain diode	characteristics				
$V_{SD}$	source-drain voltage	$I_S$ = 300 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	0.48	0.77	1.2	V
TR2 (P-cha	nnel), Static characteristic	s				,
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = -250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-20	-	-	V
		ı .				

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 °C$		-0.5	-0.8	-1.3	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C		-	-	-1	μA
		V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C		-	-	-10	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; -40 °C < T <sub>j</sub> < 150 °C		-	-	10	μA
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; -40 °C < T <sub>j</sub> < 150 °C		-	-	-10	μA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; $I_D$ = -400 mA; $T_j$ = 25 °C		-	670	850	mΩ
	resistance	$V_{GS}$ = -4.5 V; $I_D$ = -400 mA; $T_j$ = 150 °C		-	1.1	1.4	Ω
		$V_{GS}$ = -2.5 V; $I_D$ = -200 mA; $T_j$ = 25 °C		-	1.2	1.5	Ω
		$V_{GS}$ = -1.8 V; $I_D$ = -10 mA; $T_j$ = 25 °C		-	1.8	2.8	Ω
g <sub>fs</sub>	transfer conductance	$V_{DS}$ = -10 V; $I_{D}$ = -200 mA; $T_{j}$ = 25 °C		-	610	-	mS
TR2 (P-cha	nnel), Dynamic characteri	stics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -10 \text{ V}; I_D = -400 \text{ mA};$		-	0.76	1.14	nC
$Q_{GS}$	gate-source charge	$V_{GS} = -4.5 \text{ V}; T_j = 25 \text{ °C}$		-	0.28	-	nC
$Q_{GD}$	gate-drain charge			-	0.18	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = -10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$		-	58	87	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C		-	21	-	pF
C <sub>rss</sub>	reverse transfer capacitance			-	12	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $R_L$ = 250 $\Omega$ ; $V_{GS}$ = -4.5 V;		-	18	36	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$		-	30	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	80	160	ns
t <sub>f</sub>	fall time			-	72	-	ns
TR2 (P-cha	nnel), Source-drain diode	characteristics			1	1	
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = -300 mA; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C		-0.48	-0.84	-1.2	V
						1	

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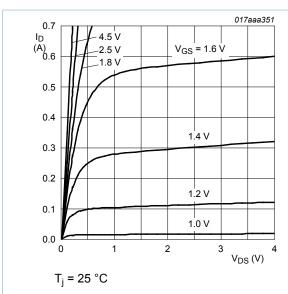
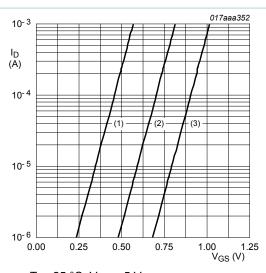


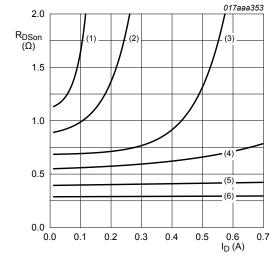
Fig. 9. TR1; Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i$  = 25 °C;  $V_{DS}$  = 5 V

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 10. TR1; Sub-threshold drain current as a function of gate-source voltage



 $T_i = 25 \,^{\circ}C$ 

(1)  $V_{GS} = 1.3 V$ 

(2)  $V_{GS} = 1.4 \text{ V}$ 

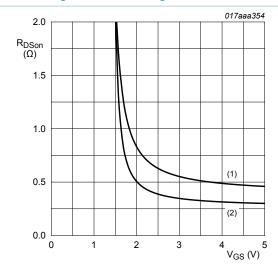
 $(3) V_{GS} = 1.6 V$ 

 $(4) V_{GS} = 1.8 V$ 

 $(5) V_{GS} = 2.5 V$ 

 $(6) V_{GS} = 4.5 V$ 

Fig. 11. TR1; Drain-source on-state resistance as a function of drain current; typical values

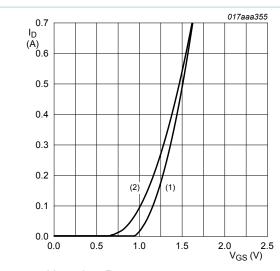


 $I_D = 400 \text{ mA}$ 

(1)  $T_i = 150 \, ^{\circ}C$ 

(2)  $T_i = 25 \,^{\circ}C$ 

Fig. 12. TR1; Drain-source on-state resistance as a function of gate-source voltage; typical values



 $V_{DS} > I_D \times R_{DSon}$ 

(1)  $T_j = 25 \,^{\circ}\text{C}$ (2)  $T_i = 150 \,^{\circ}\text{C}$ 

Fig. 13. TR1; Transfer characteristics: drain current as a function of gate-source voltage; typical values

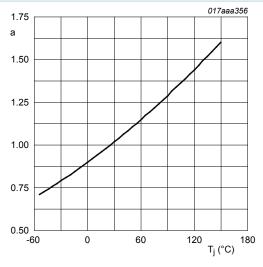
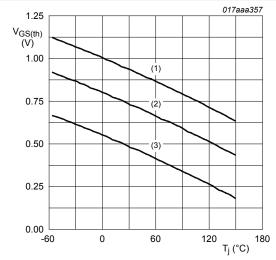


Fig. 14. TR1; Normalized drain-source on-state resistance as a function of junction temperature; typical values

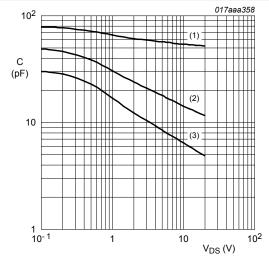
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D$  = 0.25 mA;  $V_{DS}$  =  $V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 15. TR1; Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig. 16. TR1; Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

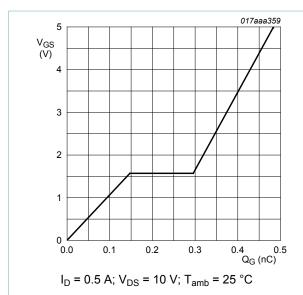


Fig. 17. TR1; Gate-source voltage as a function of gate charge; typical values

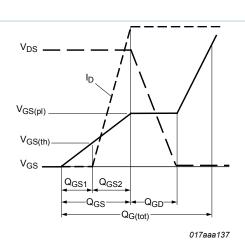
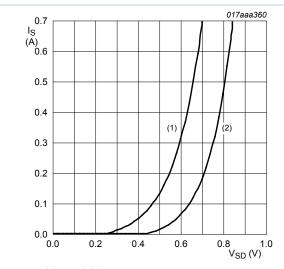


Fig. 18. Gate charge waveform definitions



 $V_{GS} = 0 V$ (1)  $T_j = 150 \,^{\circ}C$ (2)  $T_i = 25 \,^{\circ}C$ 

Fig. 19. TR1; Source current as a function of sourcedrain voltage; typical values

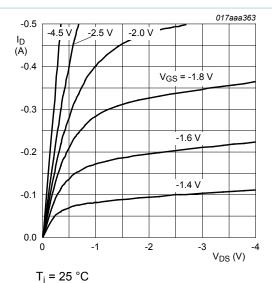
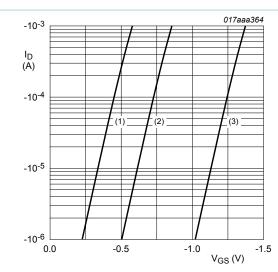


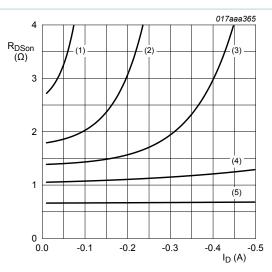
Fig. 20. TR2; Output characteristics: drain current as a function of drain-source voltage; typical values



$$T_i$$
 = 25 °C;  $V_{DS}$  = -5  $V$ 

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 21. TR2; Sub-threshold drain current as a function of gate-source voltage



$$(1) V_{GS} = -1.5 V$$

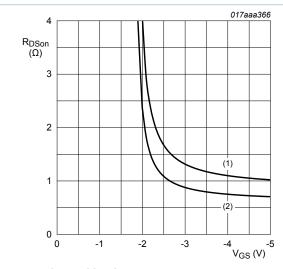
$$(2) V_{GS} = -1.8 V$$

$$(3) V_{GS} = -2.0 V$$

$$(4) V_{GS} = -2.5 V$$

$$(5) V_{GS} = -4.5 V$$

Fig. 22. TR2; Drain-source on-state resistance as a function of drain current; typical values

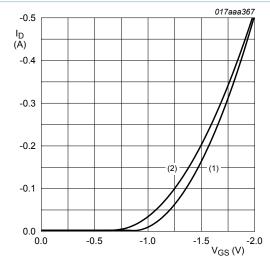


 $I_D = -400 \text{ mA}$ 

(1) 
$$T_i = 150 \, ^{\circ}C$$

(2) 
$$T_i = 25 \, ^{\circ}C$$

Fig. 23. TR2; Drain-source on-state resistance as a function of gate-source voltage; typical values



 $V_{DS} > I_{D} \times R_{DSon}$ 

(1) 
$$T_i = 25 \,^{\circ}\text{C}$$

(2) 
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig. 24. TR2; Transfer characteristics: drain current as a function of gate-source voltage; typical values

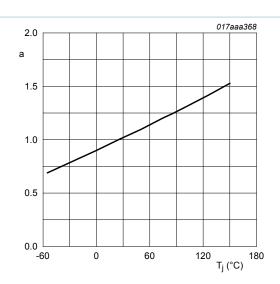
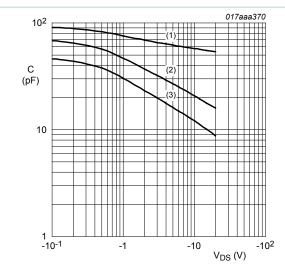


Fig. 25. TR2; Normalized drain-source on-state resistance as a function of ambient temperature; typical values

$$\mathbf{a} = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



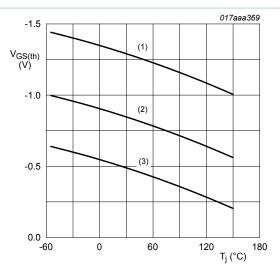
 $f = 1 MHz; V_{GS} = 0 V$ 

(1) C<sub>iss</sub>

(2) C<sub>oss</sub>

(3) C<sub>rss</sub>

Fig. 27. TR2; Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



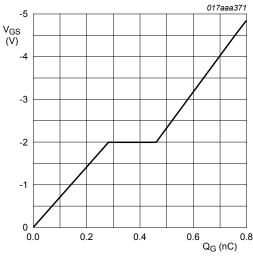
 $I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$ 

(1) maximum values

(2) typical values

(3) minimum values

Fig. 26. TR2; Gate-source threshold voltage as a function of junction temperature



 $I_D$  = -0.4 A;  $V_{DD}$  = -10 V;  $T_{amb}$  = 25 °C

Fig. 28. TR2; Gate-source voltage as a function of gate charge; typical values

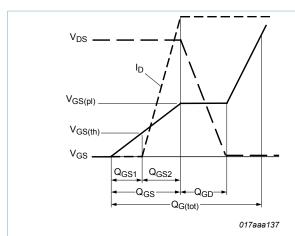


Fig. 29. Gate charge waveform definitions

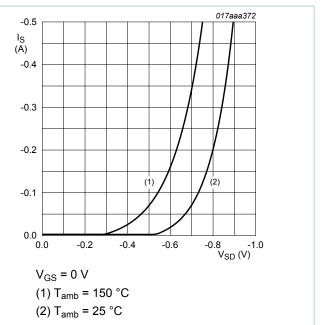
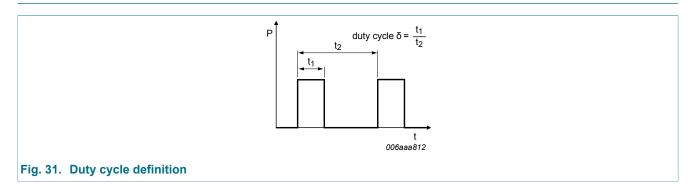


Fig. 30. TR2; Source current as a function of sourcedrain voltage; typical values

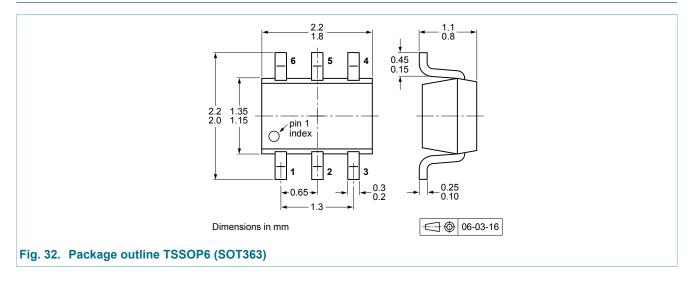
# 11. Test information



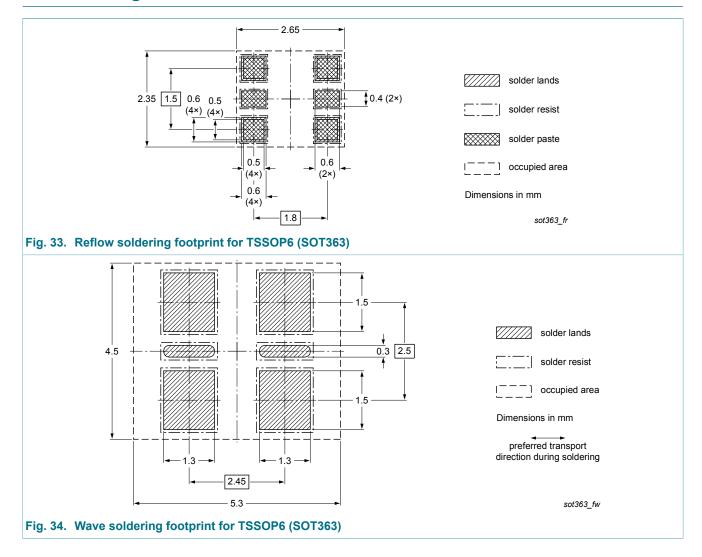
# 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

# 12. Package outline



# 13. Soldering



# 14. Revision history

# Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMGD290UCEA v.3	20140328	Product data sheet	-	PMGD290UCEA v.2
Modifications:	Table 7: I <sub>GSS</sub> param	eter unit corrected		
PMGD290UCEA v.2	20130418	Product data sheet	-	PMGD290UCEA v.1
PMGD290UCEA v.1	20130415	Product data sheet	-	-

# 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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